

74ALVC125-Q100

Quad buffer/line driver; 3-state

Rev. 1 — 28 June 2013

Product data sheet

1. General description

The 74ALVC125-Q100 is a quad non-inverting buffer/line driver with 3-state outputs. The output enable input ($\overline{nOE}$) controls the 3 state outputs (nY). A HIGH on the $\overline{nOE}$ pin causes the outputs to assume a high-impedance OFF-state.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 3) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 3)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$
- Wide supply voltage range from 1.65 V to 3.6 V
- 3.6 V tolerant inputs/outputs
- CMOS low power consumption
- Direct interface with TTL levels (2.7 V to 3.6 V)
- Power-down mode
- Latch-up performance exceeds 250 mA
- Complies with JEDEC standards:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8B/JESD36 (2.7 V to 3.6 V)
- ESD protection:
 - ◆ MIL-STD-883C, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pF}$, $R = 0\text{ }\Omega$)

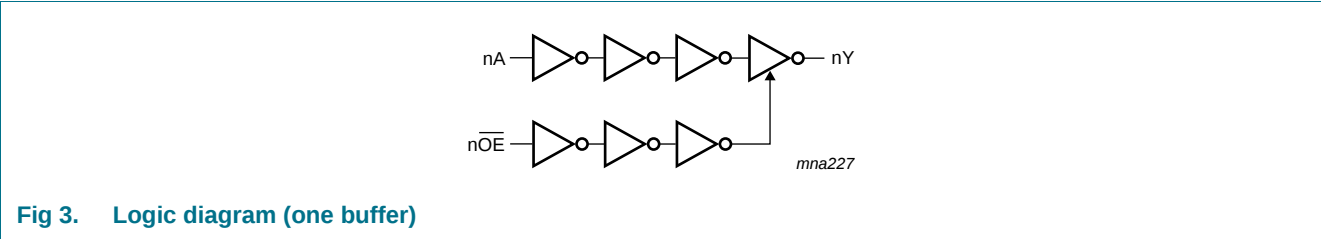
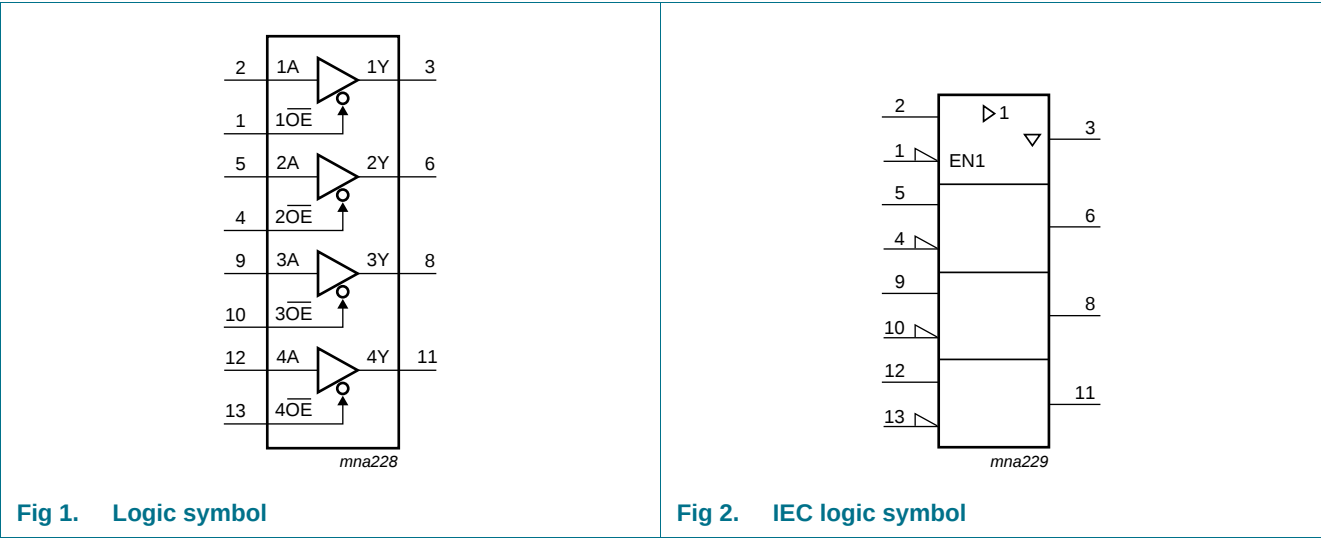


3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74ALVC125D-Q100	−40 °C to +85 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74ALVC125PW-Q100	−40 °C to +85 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74ALVC125BQ-Q100	−40 °C to +85 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads;14 terminals; body 2.5 x 3 x 0.85 mm	SOT762-1

4. Functional diagram



5. Pinning information

5.1 Pinning

74ALVC125-Q100

aaa-008233

74ALVC125-Q100

terminal 1 index area

aaa-008234

Transparent top view

(1) The die substrate is attached to this pad using conductive die attach material. It cannot be used as a supply pin or input.

Fig 4. Pin configuration SO14 and TSSOP14

Fig 5. Pin configuration DHVQFN14

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
nA	2, 5, 9, 12	data input
nY	3, 6, 8, 11	bus output
nOE	1, 4, 10, 13	output enable (active LOW)
V _{CC}	14	supply voltage
GND	7	ground (0 V)

6. Functional description

Table 3. Function table^[1]

Input		Output
nOE	nA	nY
L	L	L
L	H	H
H	X	Z

[1] H = HIGH voltage level
 L = LOW voltage level
 X= don't care
 Z = high-impedance OFF-state

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
I_{IK}	input clamping current	$V_I < 0$ V	-50	-	mA
V_I	input voltage		[1] -0.5	+4.6	V
I_{OK}	output clamping current	$V_O > V_{CC}$ or $V_O < 0$ V	-	± 50	mA
V_O	output voltage	output HIGH or LOW state	[1] [2] -0.5	$V_{CC} + 0.5$	V
		output 3-state	-0.5	+4.6	V
		Power-down mode, $V_{CC} = 0$ V	[2] -0.5	+4.6	V
I_O	output current	$V_O = 0$ V to V_{CC}	-	± 50	mA
I_{CC}	supply current		-	100	mA
I_{GND}	ground current		-100	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +85 °C	[3] -	500	mW

[1] The minimum input voltage ratings may be exceeded if the input current ratings are observed.

[2] When $V_{CC} = 0$ V (power-down mode), the output voltage can be 3.6 V in normal operation.

[3] For SO14 packages: above 70 °C derate linearly with 8 mW/K.
 For TSSOP14 packages: above 60 °C derate linearly with 5.5 mW/K.
 For DHVQFN20 packages: above 60 °C derate linearly with 4.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		1.65	3.6	V
V_I	input voltage		0	3.6	V
V_O	output voltage	output HIGH or LOW state	0	V_{CC}	V
		output 3-state	0	3.6	V
		power-down mode; $V_{CC} = 0$ V	0	3.6	V
T_{amb}	ambient temperature	in free air	-40	+85	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.65$ V to 2.7 V	0	20	ns/V
		$V_{CC} = 2.7$ V to 3.6 V	0	10	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			Unit
			Min	Typ ^[1]	Max	
V_{IH}	HIGH-level input voltage	$V_{CC} = 1.65$ V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3$ V to 2.7 V	1.7	-	-	V
		$V_{CC} = 2.7$ V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 1.65$ V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3$ V to 2.7 V	-	-	0.7	V
		$V_{CC} = 2.7$ V to 3.6 V	-	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -100$ μ A; $V_{CC} = 1.65$ V to 3.6 V	$V_{CC} - 0.2$	-	-	V
		$I_O = -6$ mA; $V_{CC} = 1.65$ V	1.25	1.51	-	V
		$I_O = -12$ mA; $V_{CC} = 2.3$ V	1.8	2.10	-	V
		$I_O = -18$ mA; $V_{CC} = 2.3$ V	1.7	2.01	-	V
		$I_O = -12$ mA; $V_{CC} = 2.7$ V	2.2	2.53	-	V
		$I_O = -18$ mA; $V_{CC} = 3.0$ V	2.4	2.76	-	V
		$I_O = -24$ mA; $V_{CC} = 3.0$ V	2.2	2.68	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 100$ μ A; $V_{CC} = 1.65$ V to 3.6 V	-	-	0.2	V
		$I_O = 6$ mA; $V_{CC} = 1.65$ V	-	0.11	0.3	V
		$I_O = 12$ mA; $V_{CC} = 2.3$ V	-	0.17	0.4	V
		$I_O = 18$ mA; $V_{CC} = 2.3$ V	-	0.25	0.6	V
		$I_O = 12$ mA; $V_{CC} = 2.7$ V	-	0.16	0.4	V
		$I_O = 18$ mA; $V_{CC} = 3.0$ V	-	0.23	0.4	V
		$I_O = 24$ mA; $V_{CC} = 3.0$ V	-	0.30	0.55	V
I_I	input leakage current	$V_{CC} = 3.6$ V; $V_I = 3.6$ V or GND	-	± 0.1	± 5	μ A

Table 6. Static characteristics ...continued

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to +85 °C			Unit
			Min	Typ ^[1]	Max	
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 1.65$ V to 3.6 V; $V_O = 3.6$ V or GND;	-	± 0.1	± 10	μ A
I_{OFF}	power-off leakage current	$V_{CC} = 0$ V; V_I or $V_O = 0$ V to 3.6 V	-	± 0.1	± 10	μ A
I_{CC}	supply current	$V_{CC} = 3.6$ V; $V_I = V_{CC}$ or GND; $I_O = 0$ A	-	0.2	10	μ A
ΔI_{CC}	additional supply current	per input pin; $V_{CC} = 3.0$ V to 3.6 V; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A	-	5	750	μ A
C_I	input capacitance		-	3.5	-	pF

[1] All typical values are measured at $V_{CC} = 3.3$ V (unless stated otherwise) and $T_{amb} = 25$ °C.

10. Dynamic characteristics

Table 7. Dynamic characteristicsVoltages are referenced to GND (ground = 0 V). For test circuit, see [Figure 8](#).

Symbol	Parameter	Conditions	–40 °C to +85 °C			Unit
			Min	Typ ^[1]	Max	
t_{pd}	propagation delay	nA to nY; see Figure 6 ^[2]				
		$V_{CC} = 1.65$ V to 1.95 V	1.3	2.4	5.3	ns
		$V_{CC} = 2.3$ V to 2.7 V	1.0	1.7	3.2	ns
		$V_{CC} = 2.7$ V	-	2.0	3.1	ns
		$V_{CC} = 3.0$ V to 3.6 V	1.1	1.8	2.8	ns
t_{en}	enable time	nOE to nY; see Figure 7 ^[2]				
		$V_{CC} = 1.65$ V to 1.95 V	1.4	3.9	6.4	ns
		$V_{CC} = 2.3$ V to 2.7 V	1.0	2.2	4.1	ns
		$V_{CC} = 2.7$ V	-	2.7	4.3	ns
		$V_{CC} = 3.0$ V to 3.6 V	1.0	1.9	3.5	ns
t_{dis}	disable time	nOE to nY; see Figure 7 ^[2]				
		$V_{CC} = 1.65$ V to 1.95 V	1.8	3.9	5.9	ns
		$V_{CC} = 2.3$ V to 2.7 V	1.0	2.1	3.4	ns
		$V_{CC} = 2.7$ V	-	2.9	4.0	ns
		$V_{CC} = 3.0$ V to 3.6 V	1.4	2.7	4.0	ns

Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V). For test circuit, see [Figure 8](#).

Symbol	Parameter	Conditions	–40 °C to +85 °C			Unit
			Min	Typ ^[1]	Max	
C _{PD}	power dissipation capacitance	per buffer; V _I = GND to V _{CC} ; V _{CC} = 3.3 V ^[3]				
		outputs HIGH or LOW state	-	27	-	pF
		outputs 3-state	-	5	-	pF

[1] Typical values are measured at T_{amb} = 25 °C

[2] t_{pd} is the same as t_{PHL} and t_{PLH}.

t_{en} is the same as t_{PZH} and t_{PZL}.

t_{dis} is the same as t_{PHZ} and t_{PLZ}.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz; f_o = output frequency in MHz

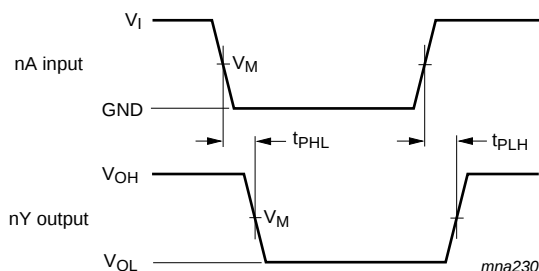
C_L = output load capacitance in pF

V_{CC} = supply voltage in Volts

N = number of inputs switching

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs

11. Waveforms

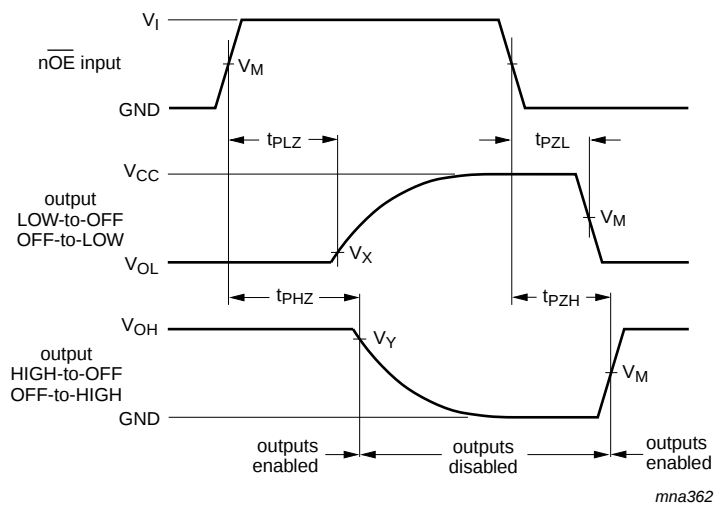


Measurement points are given in [Table 8](#).

V_{OL} and V_{OH} are the typical output voltage levels that occur with the output load.

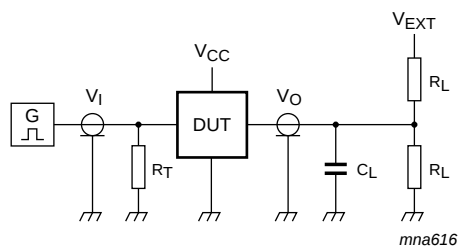
Fig 6. Input nA to output nY propagation delay times**Table 8. Measurement points**

Supply voltage	Input	Output		
V _{CC}	V _M	V _M	V _x	V _y
1.65 V to 1.95 V	0.5V _{CC}	0.5V _{CC}	V _{OL} + 0.15 V	V _{OH} – 0.15 V
2.3 V to 2.7 V	0.5V _{CC}	0.5V _{CC}	V _{OL} + 0.15 V	V _{OH} – 0.15 V
2.7 V	1.5 V	1.5 V	V _{OL} + 0.3 V	V _{OH} – 0.3 V
3.0 V to 3.6 V	1.5 V	1.5 V	V _{OL} + 0.3 V	V _{OH} – 0.3 V



Measurement points are given in [Table 8](#).
 V_{OL} and V_{OH} are the typical output voltage levels that occur with the output load.

Fig 7. Enable and disable times



Test data is given in [Table 9](#).
Definitions for test circuit:
 R_L = Load resistance.
 C_L = Load capacitance including jig and probe capacitance.
 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.
 V_{EXT} = External voltage for measuring switching times.

Fig 8. Test circuitry for switching times

Table 9. Test data

Supply voltage	Input		Load		V _{EXT}		
	V _I	t _r , t _f	C _L	R _L	t _{PLH} , t _{PHL}	t _{PLZ} , t _{PZL}	t _{PHZ} , t _{PZH}
1.65 V to 1.95 V	V _{CC}	≤ 2.0 ns	30 pF	1 kΩ	open	2 × V _{CC}	GND
2.3 V to 2.7 V	V _{CC}	≤ 2.0 ns	30 pF	500 Ω	open	2 × V _{CC}	GND
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	6 V	GND
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	6 V	GND

12. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm SOT108-1

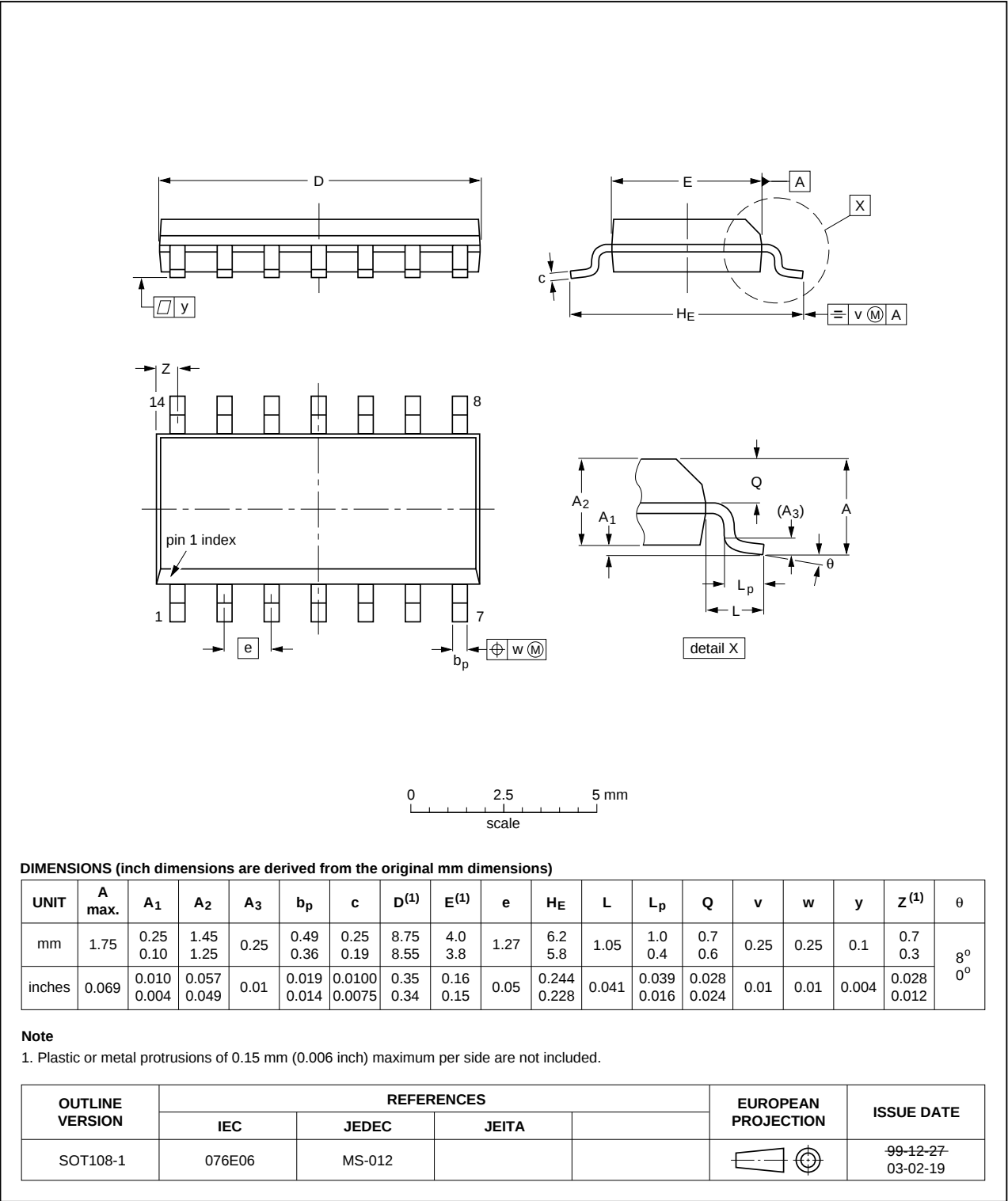


Fig 9. Package outline SOT108-1 (SO14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1

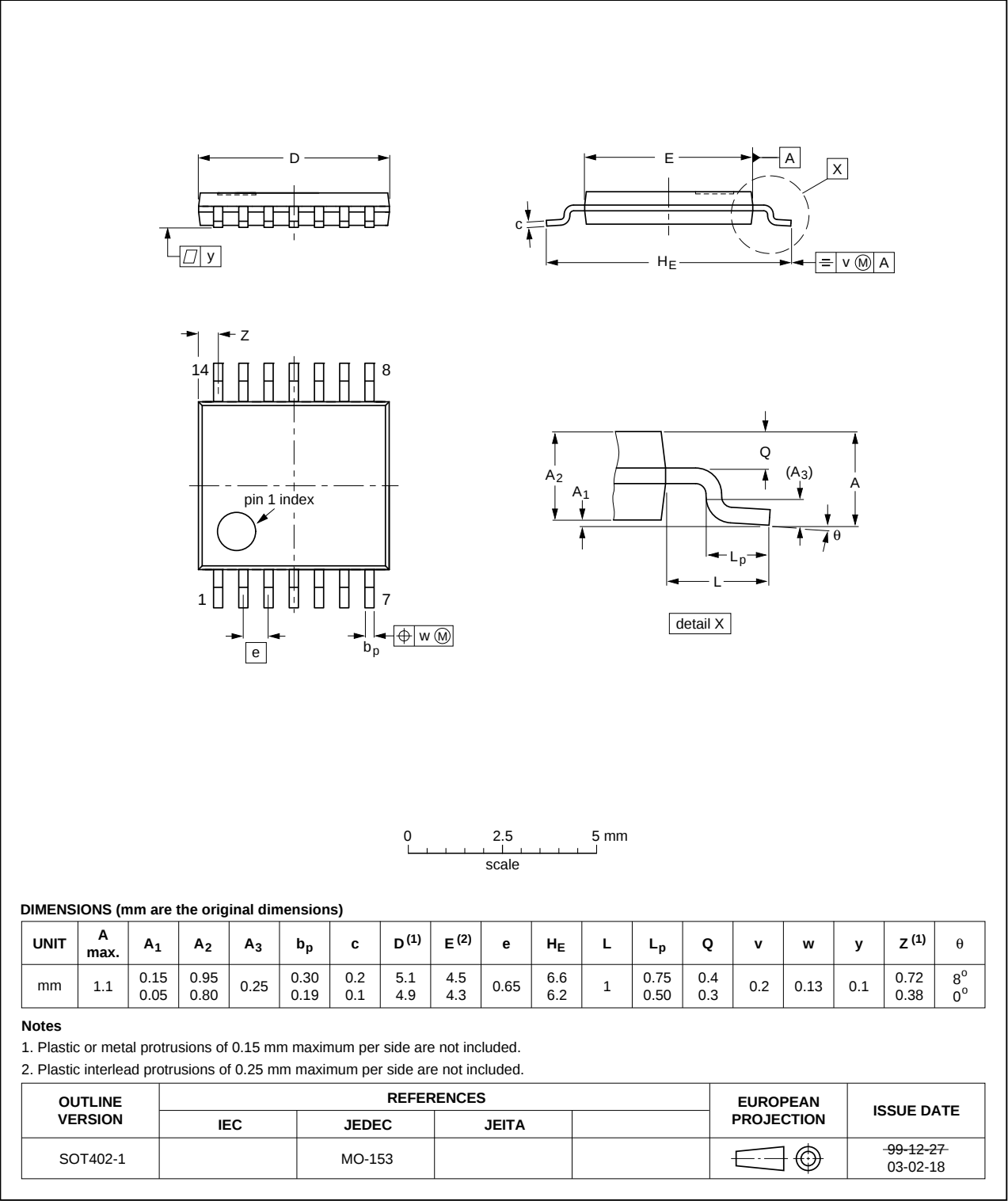


Fig 10. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1

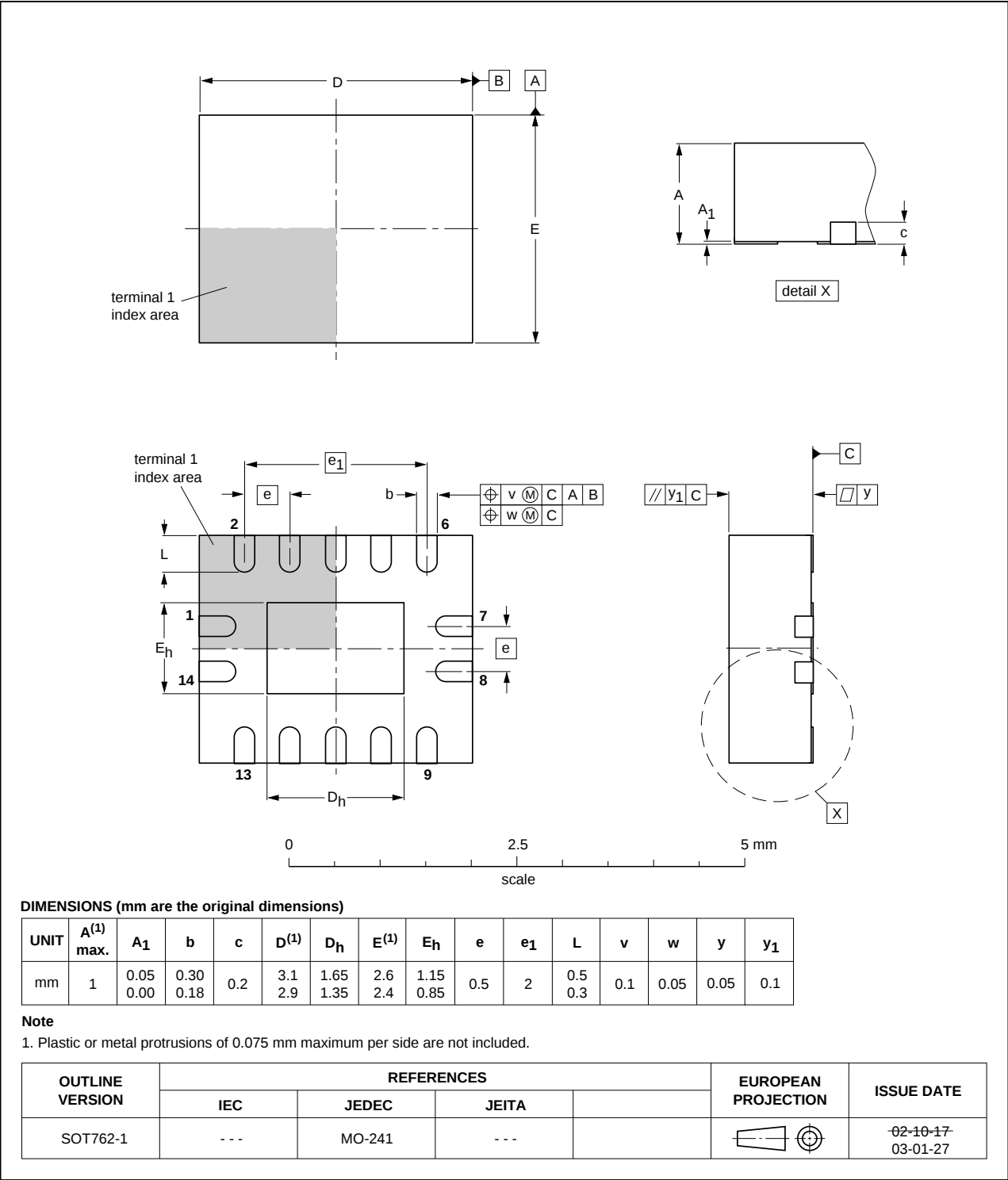


Fig 11. Package outline SOT762-1 (DHVQFN14)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MIL	Military
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74ALVC125_Q100 v.1	20130628	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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